

Applicant: Leonard Forbes

Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND
SOLID PHASE EPITAXIAL REGROWTH

Docket No.: 303.229US2
Filed: August 11, 1998
Examiner: Mark Prenty
Customer No.: 21186



Serial No.: 09/132157
Due Date: October 9, 2003
Group Art Unit: 2822
Confirmation No.: 8931

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MS Non-Fee Amendment
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P.O. Box 1450
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We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
☒ An Amendment and Response (10 Pages).

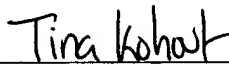
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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
Customer Number 21186

By: 
Atty: David C. Peterson
Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Non-Fee Amendment, Commissioner for Patents, P.O.Box 1450, Alexandria, VA 22313-1450, on this 9 day of October, 2003.

Name



Signature



SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
(GENERAL)

Customer Number 21186

S/N 09/132157

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes

Examiner: Mark Prently

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AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Applicant has reviewed the Office Action mailed on July 9, 2003. Please amend the above-identified patent application as follows.

#41 / *Amend J*
Q Ford
10/21/03
PATENT

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